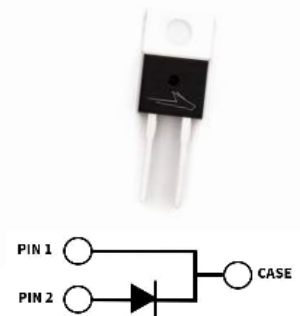


# C3D08060A

## Description

With the performance advantages of a Silicon Carbide (SiC) Schottky Barrier diode, power electronics systems can expect to meet higher efficiency standards than Si-based solutions, while also reaching higher frequencies and power densities. SiC diodes can be easily paralleled to meet various application demands, without concern of thermal runaway. In combination with the reduced cooling requirements and improved thermal performance of SiC products, SiC diodes are able to provide lower overall system costs in a variety of diverse applications.



Package Types: TO-220-2  
Marking: C3D08060A

### Features

- Low Forward Voltage ( $V_F$ ) Drop with Positive Temperature Coefficient
- Zero Reverse Recovery Current / Forward Recovery Voltage
- Temperature-Independent Switching Behavior

### Applications

- Industrial Switched Mode Power Supplies
- Uninterruptible & AUX Power Supplies
- Boost for PFC & DC-DC Stages
- Solar Inverters

## Maximum Ratings ( $T_c = 25^\circ\text{C}$ Unless Otherwise Specified)

| Parameter                                 | Symbol      | Value | Unit | Test Conditions   | Notes  |
|---|-------------|-------|------|---|--------|
| Repetitive Peak Reverse Voltage           | $V_{RRM}$   | 600   | V    |   |        |
| DC Blocking Voltage                       | $V_{DC}$    | 600   |      |   |        |
| Continuous Forward Current                | $I_F$       | 24    | A    | $T_J = 25^\circ\text{C}$                                      | Fig. 3 |
|   |             | 11    |      | $T_J = 135^\circ\text{C}$                                     |        |
|   |             | 8     |      | $T_J = 152^\circ\text{C}$                                     |        |
| Repetitive Peak Forward Surge Current     | $I_{FRM}$   | 37.5  | A    | $T_c = 25^\circ\text{C}, t_p = 10\text{ ms, Half Sine Wave}$  |        |
|   |             | 25.5  |      | $T_c = 110^\circ\text{C}, t_p = 10\text{ ms, Half Sine Wave}$ |        |
| Non-Repetitive Forward Surge Current      | $I_{FSM}$   | 71    | A    | $T_c = 25^\circ\text{C}, t_p = 10\text{ ms, Half Sine Wave}$  | Fig. 8 |
|   |             | 60    |      | $T_c = 110^\circ\text{C}, t_p = 10\text{ ms, Half Sine Wave}$ |        |
| Non-Repetitive Peak Forward Surge Current | $I_{F,Max}$ | 650   | A    | $T_c = 25^\circ\text{C}, t_p = 10\text{ }\mu\text{s, Pulse}$  |        |
|   |             | 530   |      | $T_c = 110^\circ\text{C}, t_p = 10\text{ }\mu\text{s, Pulse}$ |        |
| Power Dissipation                         | $P_{tot}$   | 107   | W    | $T_J = 25^\circ\text{C}$                                      | Fig. 4 |
|   |             | 46.5  |      | $T_J = 110^\circ\text{C}$                                     |        |

## Electrical Characteristics

| Parameter                 | Symbol | Typ. | Max. | Unit          | Test Conditions   | Notes  |
|---------------------------|--------|------|------|---------------|---|--------|
| Forward Voltage           | $V_F$  | 1.5  | 1.8  | V             | $I_F = 8 \text{ A}, T_j = 25 \text{ }^\circ\text{C}$                      | Fig. 1 |
|                           |        | 2.1  | 2.4  |               | $I_F = 8 \text{ A}, T_j = 175 \text{ }^\circ\text{C}$                     |        |
| Reverse Current           | $I_R$  | 8.5  | 42.5 | $\mu\text{A}$ | $V_R = 600 \text{ V}, T_j = 25 \text{ }^\circ\text{C}$                    | Fig. 2 |
|                           |        | 17   | 170  |               | $V_R = 600 \text{ V}, T_j = 175 \text{ }^\circ\text{C}$                   |        |
| Total Capacitive Charge   | $Q_C$  | 20   |      | nC            | $V_R = 400 \text{ V}, T_j = 25 \text{ }^\circ\text{C}$                    | Fig. 5 |
| Total Capacitance         | C      | 395  |      | pF            | $V_R = 0 \text{ V}, T_j = 25 \text{ }^\circ\text{C}, f = 1 \text{ MHz}$   | Fig. 6 |
|                           |        | 37   |      |               | $V_R = 200 \text{ V}, T_j = 25 \text{ }^\circ\text{C}, f = 1 \text{ MHz}$ |        |
|                           |        | 32   |      |               | $V_R = 400 \text{ V}, T_j = 25 \text{ }^\circ\text{C}, f = 1 \text{ MHz}$ |        |
| Capacitance Stored Energy | $E_C$  | 3.0  |      | $\mu\text{J}$ | $V_R = 400 \text{ V}$   | Fig. 7 |

### Notes:

SiC Schottky Diodes are majority carrier devices, so there is no reverse recovery charge.

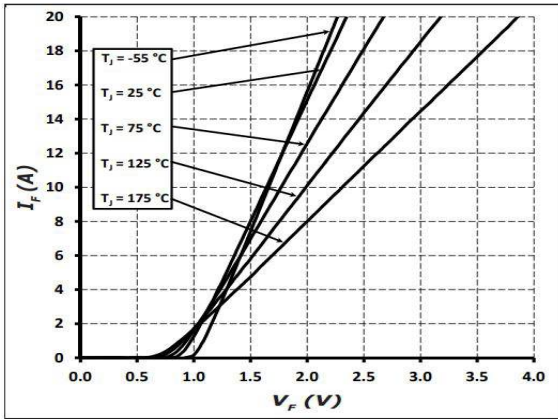
## Thermal & Mechanical Characteristics

| Parameter                                      | Symbol                 | Value       | Unit                        | Notes      |
|--|------------------------|-------------|-----------------------------|------------|
| Thermal Resistance, Junction to Case (Typical) | $R_{\theta, JC (TYP)}$ | 1.4         | $^\circ\text{C} / \text{W}$ |            |
| Junction Temperature                           | $T_j$                  | -55 to +175 | $^\circ\text{C}$            |            |
| Case & Storage Temperature                     | $T_c$                  | -55 to +175 |                             |            |
| TO-220 Mounting Torque                         | -                      | 1           | Nm                          | M3 Screw   |
|  |                        | 8.8         | lbf-in                      | 6-32 Screw |

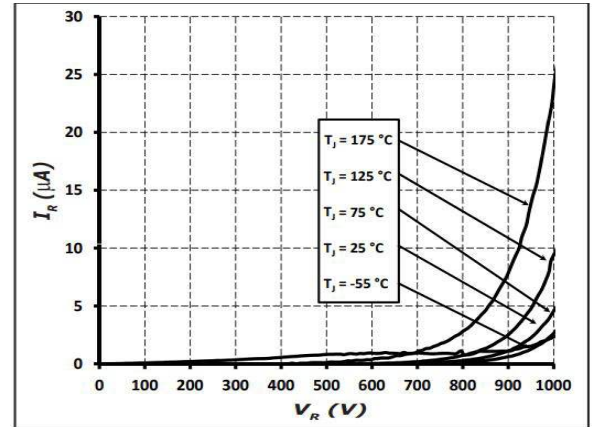
## Electrostatic Discharge (ESD) Classifications

| Parameter           | Symbol | Notes                              |
|---------------------|--------|------------------------------------|
| Human Body Model    | HBM    | Class 3B ( $\geq 8000 \text{ V}$ ) |
| Charge Device Model | CDM    | Class C3 ( $\geq 1000 \text{ V}$ ) |

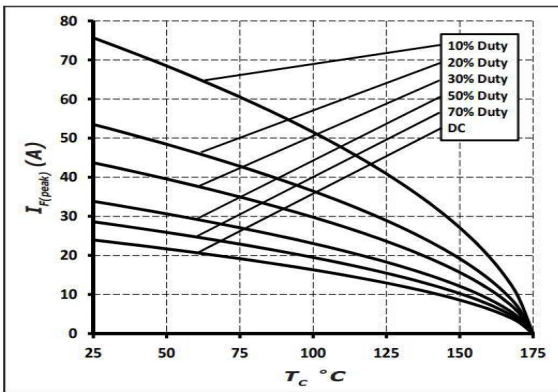
Typical Performance



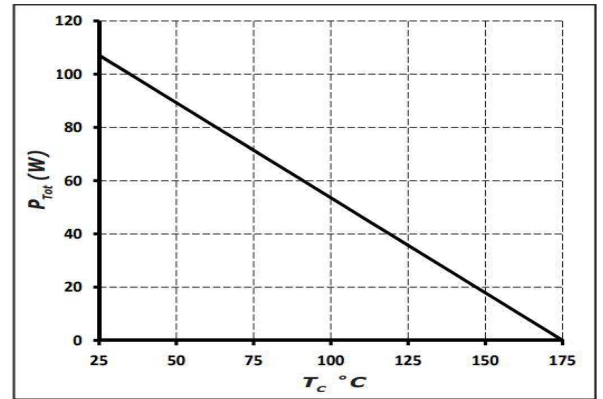
**Figure 1**  
Forward Characteristics



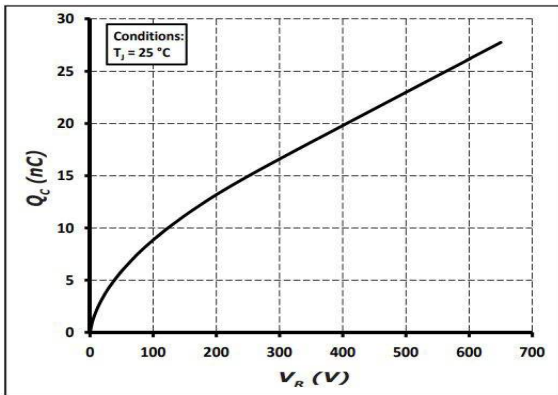
**Figure 2**  
Reverse Characteristics



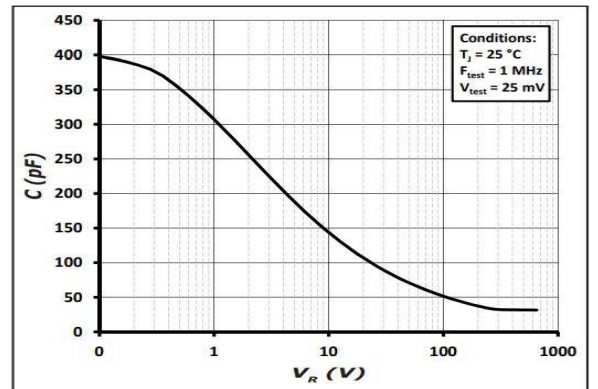
**Figure 3**  
Current Derating



**Figure 4**  
Power Derating

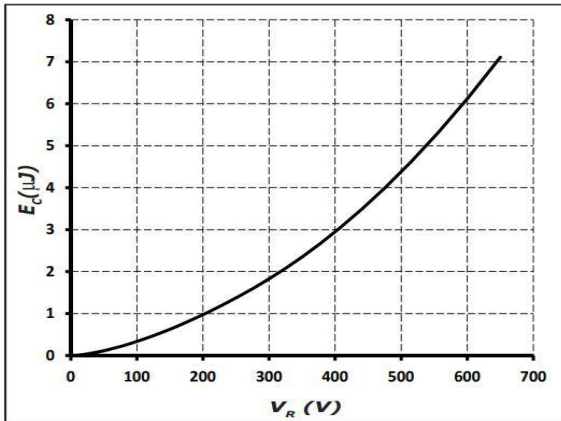


**Figure 5**  
Total Capacitance Charge vs. Reverse Voltage

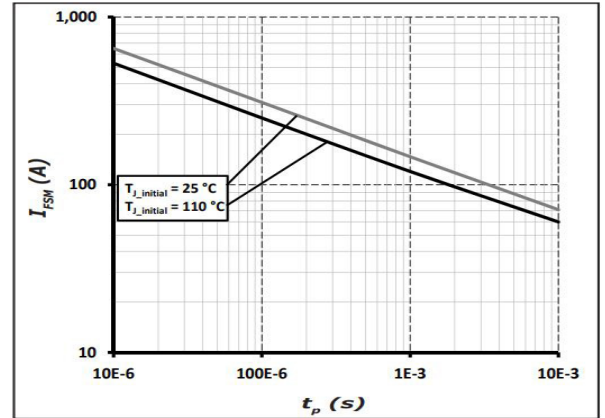


**Figure 6**  
Capacitance vs. Reverse Voltage

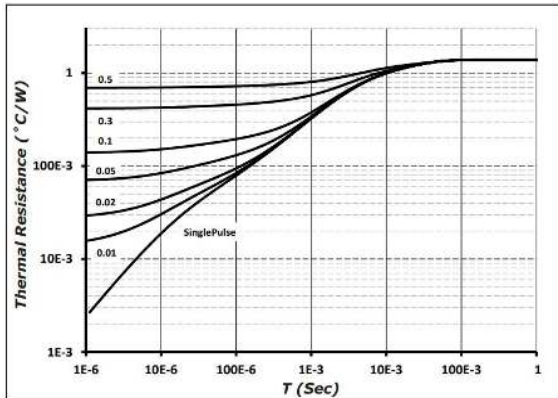
Typical Performance



**Figure 7**  
Capacitance Stored Energy



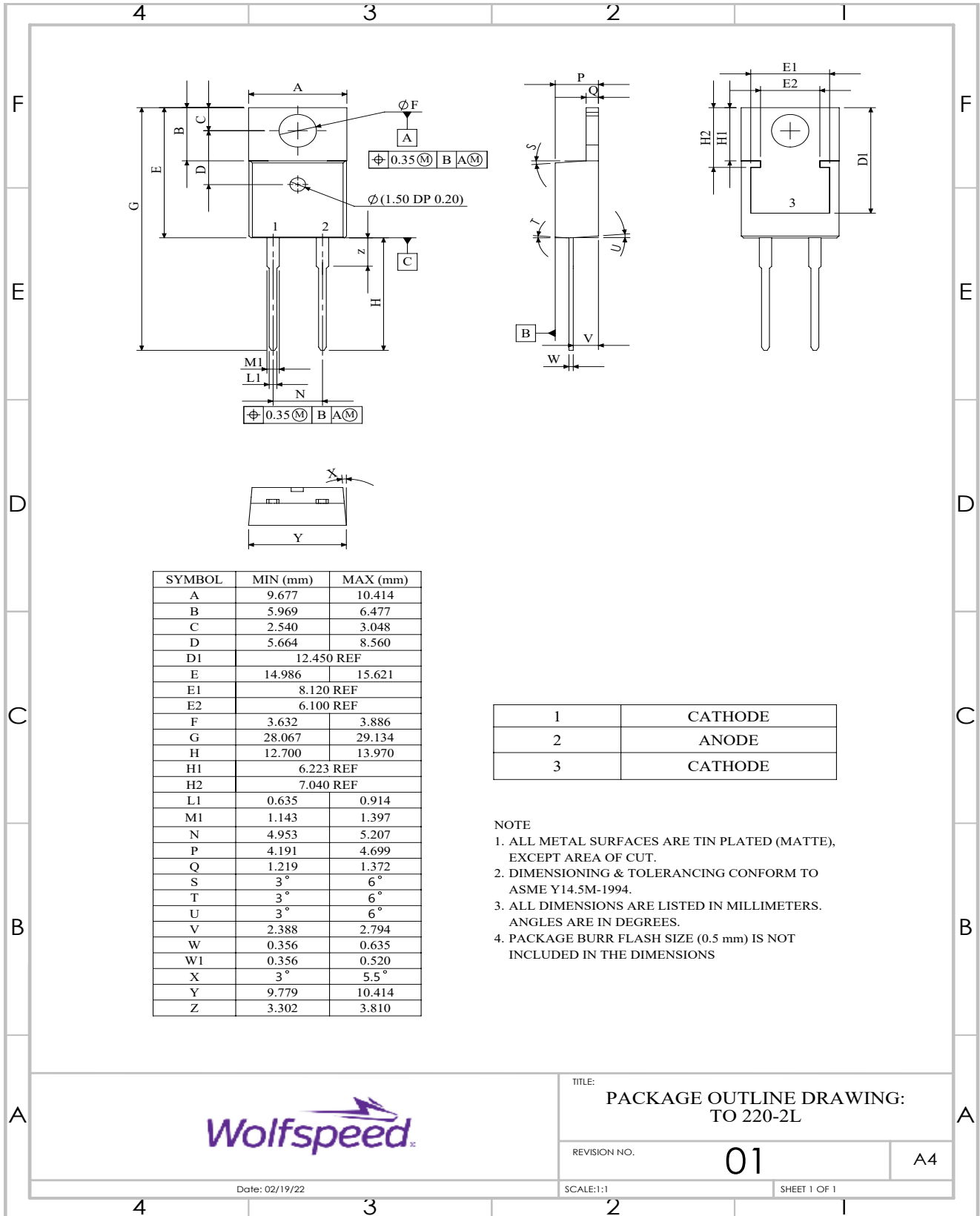
**Figure 8**  
Non-Repetitive Peak Forward Surge Current vs. Pulse Duration



**Figure 9**  
Transient Thermal Impedance

### Package Dimensions & Pin-Out

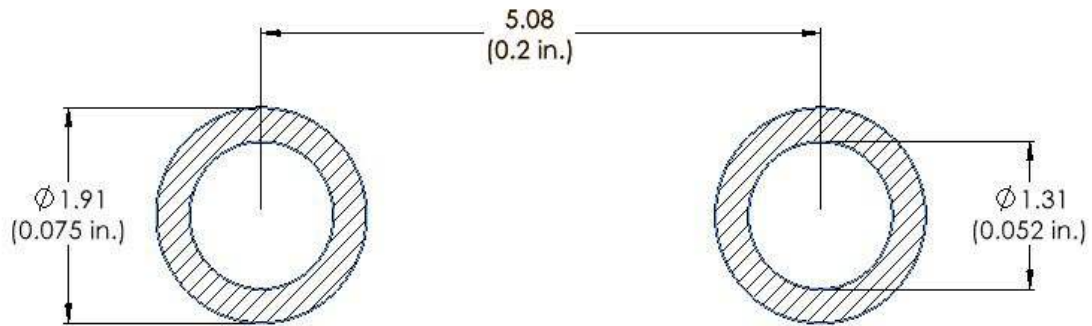
Package: TO-220-2



## Recommended Solder Pad Layout

Primary dimensions shown in mm.

Learn more about recommended soldering profiles in [this application note](#).



## Product Ordering Information

| Order Number | Packing Type |
|--------------|--------------|
| C3D08060A    | Tube         |

Learn more about power device packing & shipment information in [this application note](#).



## Revision History

| Document Version | Date of Release | Description of Changes                       |
|------------------|-----------------|--|
| 1                | August-2016     | Initial Release                              |
| 9                | January-2023    | Update Package Drawing<br>Update Landing Pad |

## Notes & Disclaimer

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